GESD0502L

Ultra Low Capacitance TVS/ESD Protection Diode

DESCRIPTION

GESD0502L is an ultra-low capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for high-speed data interfaces. With typical capacitance of 0.2pF (I/O to I/O) only, GESD0502L is designed to protect parasitic-sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 (±15kV air, ±8kV contact discharge), IEC 61000-4-4 (electrical fast transient - EFT) (40A, 5/50 ns), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc.

GESD0502L uses small DFN1006-3L package. Each GESD0502L device can protect two high-speed data lines. The combined features of low capacitance, small size and high ESD robustness make GESD0502L ideal for high-speed data port and high-frequency line applications. The low clamping voltage of the GESD0502L guarantees a minimum stress on the protected IC.

FEATURES

- ✧Transient protection for high-speed data lines
  - IEC 61000-4-2 (ESD) ±15kV (Air)
  - ±8kV (Contact)
  - IEC 61000-4-4 (EFT) 40A (5/50 ns)
  - Cable Discharge Event (CDE)
- ✧Small package (1.0mm×0.6mm×0.5mm)
- ✧Protects two data lines
- ✧Low capacitance: 0.2pF Typical (I/O-I/O)
- ✧Low leakage current
- ✧Low clamping voltage

MACHANICAL DATA

- ✧DFN1006-3L package
- ✧Flammability Rating: UL 94V-0
- ✧Packaging: Tape and Reel
- ✧High temperature soldering guaranted:260/10s
- ✧Reel size: 7 inch

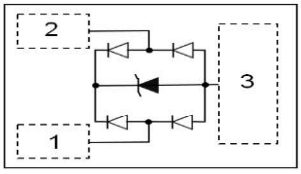
ORDERING INFORMATION

- ✧Device: GESD0502L
- ✧Package: DFN1006-3L
- ✧Marking: 52L
- ✧Material: Halogen free
- ✧Packing: Tape & Reel
- ✧Quantity per reel: 10,000pcs

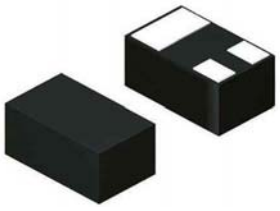
APPLICATIONS

- ✧Serial ATA
- ✧Desktops, Servers and Notebooks
- ✧PCI Express
- ✧MDDI Ports
- ✧USB Data Line Protection
- ✧Display Ports
- ✧Digital Visual Interfaces (DVI)

PIN CONFIGURATION



PACKAGE OUTLINE



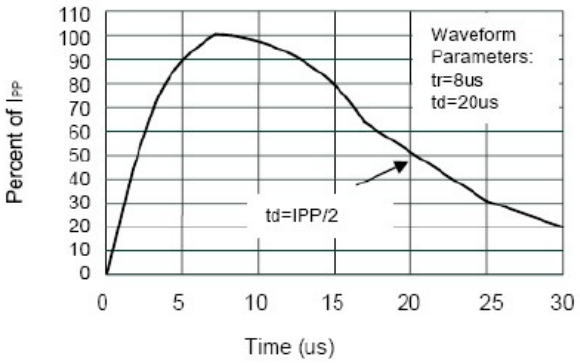
ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Units
P_{PP}	Peak Pulse Power (8/20μs)	60	W
V_{ESD}	ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	±20 ±20	kV
T_{OPT}	Operating Temperature	-55/+125	°C
T_{STG}	Storage Temperature	-55/+150	°C

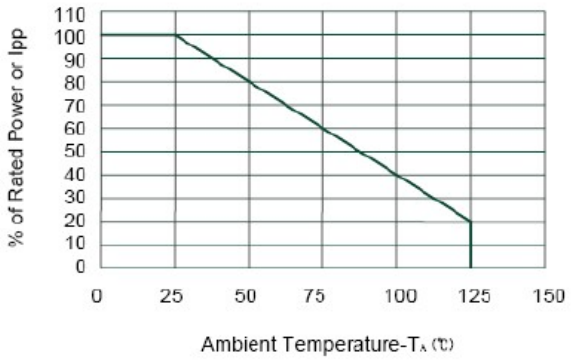
ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Symbol	Parameter	Test Condition	Min	Typ	Max	Units
V_{RWM}	Reverse Working Voltage	I/O to GND			5.0	V
V_{BR}	Reverse Breakdown Voltage	I_T = 1mA Between I/O and GND	6.0			V
I_R	Reverse Leakage Current	V_{RWM} = 5V Between I/O and GND			100	nA
V_C	Clamping Voltage	I_{PP} = 1A, t_p = 8/20μs Between I/O and GND			10	V
		I_{PP} = 4A, t_p = 8/20μs Between I/O and GND			15	V
V_F	Forward Voltage	I_T = 10mA Between I/O and GND			1.2	V
C_T	Total Capacitance	V_R = 0V, f = 1MHz Between I/O and GND		0.4	0.6	pF
		V_R = 0V, f = 1MHz Between I/O and I/O		0.2	0.3	pF

ELECTRICAL CHARACTERISTICS CURVE

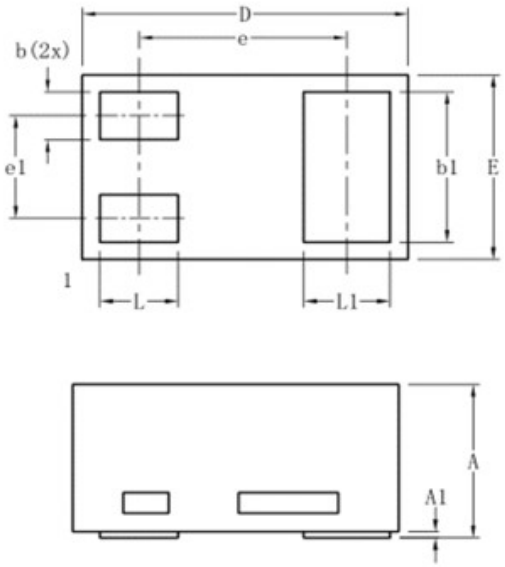


Pulse Waveform



Power Derating Curve

DFN1006-3L PACKAGE OUTLINE DIMENSIONS



	MILLIMETER		
SYMBOL	MIN	MON	MAX
D	0.95	1	1.05
E	0.55	0.6	0.65
e		0.65	
e1		0.35	
L/L1	0.2	0.25	0.3
b		0.15	
b1	0.45	0.5	0.55
A	0.46	0.48	0.5
A1	0	0.02	0.05